

# Low Voltage, 300 MHz Quad 2:1 Mux Analog HDTV Audio/Video Switch

# ADG794

#### **FEATURES**

Bandwidth: 300 MHz Low insertion loss and on resistance: 5 Ω typical On resistance flatness: 0.68 Ω typical Single 3 V/5 V supply operation Low quiescent supply current: 1 nA typical Fast switching times: tow, 7 ns

toff, 5 ns TTL/CMOS compatible

### **APPLICATIONS**

RGB switches HDTV DVD-R Audio/video switches

### **GENERAL DESCRIPTION**

The ADG794 is a monolithic CMOS device comprising four 2:1 multiplexer/demultiplexers with high impedance outputs. The CMOS process provides low power dissipation yet gives high switching speed and low on resistance. The on resistance variation is typically less than 1.2  $\Omega$  over the input signal range.

The bandwidth of the ADG794 is typically 300 MHz and this, coupled with low distortion (typically 0.68%), makes the part suitable for switching analog audio/video signals.

The ADG794 operates from a single 3.3 V/5 V supply and is TTL logic compatible. The switches are controlled by the logic inputs IN and  $\overline{\text{EN}}$  as shown in Table 4. The  $\overline{\text{EN}}$  pin allows the user to disable all switches.

### FUNCTIONAL BLOCK DIAGRAM



These switches conduct equally well in both directions when on. In the off condition, signal levels up to the supplies are blocked. The ADG794 switches exhibit break-before-make switching action.

The ADG794 is available in a 16-pin QSOP package.

### **PRODUCT HIGHLIGHTS**

- 1. Wide bandwidth: 300 MHz.
- 2. Ultralow power dissipation.
- 3. Crosstalk is typically -70 dB at 10 MHz.
- 4. Off isolation is typically –65 dB at 10 MHz.

#### Rev. 0

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# TABLE OF CONTENTS

Specifications	. 3
Single Supply	. 3
Absolute Maximum Ratings	. 5
ESD Caution	. 5
Pin Configuration and Function Descriptions	. 6
Terminology	. 7

Typical Performance Characteristics
Typical Application8
Test Circuits9
Outline Dimensions11
Ordering Guide11

### **REVISION HISTORY**

10/04—Revision 0: Initial Version

# **SPECIFICATIONS**

## SINGLE SUPPLY

 $V_{\text{DD}}$  = 5 V  $\pm$  10%, GND = 0 V. All specifications  $T_{\text{MIN}}$  to  $T_{\text{MAX}}$  , unless otherwise noted.

### Table 1.

B Version <sup>1</sup>					
Parameter	25°C	T <sub>MIN</sub> to T <sub>MAX</sub>	Unit	Test Conditions/Comments	
ANALOG SWITCH					
Analog Signal Range		0 to 2.5	V		
On Resistance (R <sub>ON</sub> )	5		Ωtyp	$V_D = 0$ V to 1 V; $I_S = -10$ mA; Figure 6	
	7	8	Ωmax		
On Resistance Match between Channels ( $\Delta R_{ON}$ )	0.4		Ωtyp	$V_D = 0 V$ to 1 V; $I_S = -10 mA$	
		1.2	Ωmax		
On Resistance Flatness (R <sub>FLAT(ON)</sub> )	0.7		Ωtyp	$V_D = 0 V$ to 1 V; $I_S = -10 mA$	
		1.35	Ωmax		
LEAKAGE CURRENTS					
Source Off Leakage, Is (Off)	±0.001		nA typ	$V_{s} = 3 V/1 V$ ; $V_{D} = 1 V/3 V$ ; Figure 7	
Drain Off Leakage, I <sub>D</sub> (Off)	±0.001		nA typ	$V_{s} = 3 V/1 V$ ; $V_{D} = 1 V/3 V$ ; Figure 7	
Channel On Leakage, I <sub>D</sub> , I <sub>S</sub> (On)	±0.001		nA typ	$V_D = V_S = 3 V/1 V$ ; Figure 8	
DIGITAL INPUTS					
Input High Voltage, V <sub>INH</sub>		2.4	V min		
Input Low Voltage, V <sub>INL</sub>		0.8	V max		
Input Current					
I <sub>INL</sub> or I <sub>INH</sub>	0.001		μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$	
		±0.1	μA max		
Digital Input Capacitance, C <sub>IN</sub>		3	pF typ		
DYNAMIC CHARACTERISTICS <sup>2</sup>					
ton, ton (EN)	7		ns typ	$C_L = 35 \text{ pF}; R_L = 50 \Omega$	
		14	ns max	$V_s = 2 V$ ; Figure 9	
toff, toff (EN)	5		ns typ	$C_{L} = 35 \text{ pF}; R_{L} = 50 \Omega$	
		8	ns max	$V_s = 2 V$ ; Figure 9	
Break-Before-Make Time Delay, t <sub>D</sub>	3		ns typ	$C_{L} = 35 \text{ pF}; R_{L} = 50 \Omega$	
·		1	ns min	$V_{s1} = V_{s2} = 2 V$ ; Figure 10	
Off Isolation	-65		dB typ	f = 10 MHz; R <sub>L</sub> = 50 Ω; Figure 12	
Channel-to-Channel Crosstalk	-70		dB typ	f = 10 MHz; R <sub>L</sub> = 50 Ω; Figure 13	
Bandwidth –3 dB	300		MHz typ	$R_L = 50 \Omega$ ; Figure 11	
Distortion	0.7		% typ	$R_L = 100 \Omega$	
Charge Injection	6		pC typ	$C_{L} = 1 \text{ nF}; V_{s} = 0 \text{ V}; Figure 14$	
Cs (Off)	6		pF typ	_	
C <sub>D</sub> (Off)	7.5		pF typ		
C <sub>D</sub> , C <sub>s</sub> (On)	13.5		pF typ		
POWER REQUIREMENTS				$V_{DD} = 5.5 \text{ V}$ ; digital inputs = 0 V or $V_{DD}$	
lod	0.001		μA typ		
		1	μA max		

<sup>1</sup> Temperature range for B Version is -40°C to +85°C.

<sup>2</sup> Guaranteed by design, not subject to production test.

 $V_{\text{DD}}$  = 3 V  $\pm$  10%, GND = 0 V. All specifications  $T_{\text{MIN}}$  to  $T_{\text{MAX}}$  unless otherwise noted.

### Table 2.

	B Version <sup>1</sup>				
Parameter	25°C	TMIN to TMAX	Unit	Test Conditions/Comments	
ANALOG SWITCH					
Analog Signal Range		0 to 1.5	V		
On Resistance (R <sub>ON</sub> )	7		Ωtyp	$V_D = 0$ V to 1 V; $I_s = -10$ mA; Figure 6	
	9.5	11	Ωmax		
On Resistance Match between Channels ( $\Delta R_{ON}$ )	0.3		Ωtyp	$V_D = 0 V$ to 1 V; $I_s = -10 mA$	
		0.9	Ωmax		
On Resistance Flatness (R <sub>FLAT(ON)</sub> )	2.6		Ωtyp	$V_D = 0 V$ to 1 V; Is = -10 mA	
		5	$\Omega$ max		
LEAKAGE CURRENTS					
Source Off Leakage, Is (Off)	±0.001		nA typ	$V_{s} = 2 V/1 V$ ; $V_{D} = 1 V/2 V$ ; Figure 7	
Drain Off Leakage, I <sub>D</sub> (Off)	±0.001		nA typ	$V_{s} = 2 V/1 V$ ; $V_{D} = 1 V/2 V$ ; Figure 7	
Channel On Leakage, I <sub>D</sub> , I <sub>S</sub> (On)	±0.001		nA typ	$V_D = V_S = 2 V/1 V$ ; Figure 8	
DIGITAL INPUTS					
Input High Voltage, VINH		2.0	V min		
Input Low Voltage, VINL		0.4	V max		
Input Current					
IINL OR INH	0.001		μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$	
		±0.1	μA max		
Digital Input Capacitance, C <sub>IN</sub>		3	pF typ		
DYNAMIC CHARACTERISTICS <sup>2</sup>					
t <sub>on</sub> , t <sub>on</sub> ( <del>EN</del> )	8		ns typ	$C_L = 35 \text{ pF}; R_L = 50 \Omega$	
		16	ns max	Vs = 1.5 V; Figure 9	
toff, toff (EN)	6		ns typ	$C_L = 35 \text{ pF}; R_L = 50 \Omega$	
		10	ns max	V <sub>s</sub> = 1.5 V; Figure 9	
Break-Before-Make Time Delay, t <sub>D</sub>	3		ns typ	$C_L = 35 \text{ pF}; R_L = 50 \Omega$	
		1	ns min	$V_{S1} = V_{S2} = 1.5 V$ ; Figure 10	
Off Isolation	-65		dB typ	$f = 10 \text{ MHz}$ ; $R_L = 50 \Omega$ ; Figure 12	
Channel-to-Channel Crosstalk	-70		dB typ	$f = 10 \text{ MHz}$ ; $R_L = 50 \Omega$ ; Figure 13	
Bandwidth –3 dB	300		MHz typ	R∟ = 50 Ω; Figure 11	
Distortion	2.6		% typ	$R_L = 100 \Omega$	
Charge Injection	4		pC typ	$C_L = 1 \text{ nF}; V_S = 0 \text{ V}; Figure 14$	
Cs (Off)	6		pF typ		
C <sub>D</sub> (Off)	7.5		pF typ		
C <sub>D</sub> , C <sub>S</sub> (On)	13.5		pF typ		
POWER REQUIREMENTS				$V_{DD} = 3.3 \text{ V}$ ; digital inputs = 0 V or $V_{DD}$	
I <sub>DD</sub>	0.001		μA typ		
		1	μA max		

 $^{\rm 1}$  Temperature range for B Version is –40°C to +85°C.  $^{\rm 2}$  Guaranteed by design, not subject to production test.

# ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$ , unless otherwise noted.

#### Table 3.

ParametersRatings $V_{DD}$ to GND $-0.3$ V to $+6$ VAnalog, Digital Inputs1 $-0.3$ V to $V_{DD} + 0.3$ V or $30$ mA, whichever occurs firstContinuous Current, S or D100 mAPeak Current, S or D $300$ mA (pulsed at 1 ms, $10\%$ duty cycle max)Operating Temperature Range Industrial (B Version) $-40^{\circ}C$ to $+85^{\circ}C$ Storage Temperature Range Junction Temperature $150^{\circ}C$ QSOP Package, Power Dissipation $\theta_{JA}$ Thermal Impedance Lead Temperature, Soldering Vapor Phase (60 s) $215^{\circ}C$ Infrared (15 s) $220^{\circ}C$		
Analog, Digital Inputs1 $-0.3 V to V_{DD} + 0.3 V or30 mA, whichever occursfirstContinuous Current, S or D100 mAPeak Current, S or D300 mA (pulsed at 1 ms,10% duty cycle max)Operating Temperature RangeIndustrial (B Version)-40^{\circ}C to +85^{\circ}CStorage Temperature RangeJunction TemperatureQSOP Package, Power Dissipation\theta_{JA} Thermal ImpedanceLead Temperature, SolderingVapor Phase (60 s)-0.3 V to V_{DD} + 0.3 V or30 mA, whichever occursfirstVation TemperatureVapor Phase (60 s)-0.3 V to V_{DD} + 0.3 V or30 mA, whichever occursfirstStorage Temperature RangeIndustrial (B Version)-40^{\circ}C to +85^{\circ}CStorage Temperature RangeIndustrial (B Version)-40^{\circ}C to +150^{\circ}CJunction TemperatureQSOP Package, Power Dissipation0 J_{A} Thermal Impedance149.97^{\circ}C/W$	Parameters	Ratings
30 mA, whichever occurs firstContinuous Current, S or D100 mAPeak Current, S or D300 mA (pulsed at 1 ms, 10% duty cycle max)Operating Temperature Range Industrial (B Version)-40°C to +85°CStorage Temperature Range Junction Temperature-65°C to +150°CJunction Temperature QSOP Package, Power Dissipation $\theta_{JA}$ Thermal Impedance Lead Temperature, Soldering Vapor Phase (60 s)215°C	V <sub>DD</sub> to GND	–0.3 V to +6 V
firstContinuous Current, S or D100 mAPeak Current, S or D300 mA (pulsed at 1 ms, 10% duty cycle max)Operating Temperature Range-40°C to +85°CIndustrial (B Version)-40°C to +85°CStorage Temperature Range-65°C to +150°CJunction Temperature150°CQSOP Package, Power Dissipation566 mWθ <sub>JA</sub> Thermal Impedance149.97°C/WLead Temperature, Soldering215°C	Analog, Digital Inputs <sup>1</sup>	-0.3 V to V <sub>DD</sub> + 0.3 V or
Continuous Current, S or D100 mAPeak Current, S or D300 mA (pulsed at 1 ms, 10% duty cycle max)Operating Temperature Range Industrial (B Version)-40°C to +85°CStorage Temperature Range-65°C to +150°CJunction Temperature QSOP Package, Power Dissipation $\theta_{JA}$ Thermal Impedance566 mWUsed Temperature, Soldering Vapor Phase (60 s)215°C		
Peak Current, S or D300 mA (pulsed at 1 ms, 10% duty cycle max)Operating Temperature Range Industrial (B Version)-40°C to +85°CStorage Temperature Range Junction Temperature-65°C to +150°CJunction Temperature QSOP Package, Power Dissipation $θ_{JA}$ Thermal Impedance Lead Temperature, Soldering Vapor Phase (60 s)300 mA (pulsed at 1 ms, 10% duty cycle max)		first
Nome10% duty cycle max)Operating Temperature Range-40°C to +85°CIndustrial (B Version)-40°C to +85°CStorage Temperature Range-65°C to +150°CJunction Temperature150°CQSOP Package, Power Dissipation566 mWθJA Thermal Impedance149.97°C/WLead Temperature, Soldering215°C	Continuous Current, S or D	100 mA
Operating Temperature Range Industrial (B Version)-40°C to +85°CStorage Temperature Range-65°C to +150°CJunction Temperature150°CQSOP Package, Power Dissipation566 mW $\theta_{JA}$ Thermal Impedance149.97°C/WLead Temperature, Soldering Vapor Phase (60 s)215°C	Peak Current, S or D	300 mA (pulsed at 1 ms,
Industrial (B Version)-40°C to +85°CStorage Temperature Range-65°C to +150°CJunction Temperature150°CQSOP Package, Power Dissipation566 mWθJA Thermal Impedance149.97°C/WLead Temperature, Soldering215°C		10% duty cycle max)
Storage Temperature Range $-65^{\circ}$ C to $+150^{\circ}$ CJunction Temperature $150^{\circ}$ CQSOP Package, Power Dissipation $566 \text{ mW}$ $\theta_{JA}$ Thermal Impedance $149.97^{\circ}$ C/WLead Temperature, Soldering $215^{\circ}$ C	Operating Temperature Range	
Junction Temperature150°CQSOP Package, Power Dissipation566 mWθ <sub>JA</sub> Thermal Impedance149.97°C/WLead Temperature, Soldering215°C	Industrial (B Version)	–40°C to +85°C
QSOP Package, Power Dissipation566 mWθJA Thermal Impedance149.97°C/WLead Temperature, Soldering215°C	Storage Temperature Range	–65°C to +150°C
θ <sub>JA</sub> Thermal Impedance149.97°C/WLead Temperature, Soldering215°C	Junction Temperature	150°C
Lead Temperature, Soldering Vapor Phase (60 s) 215°C	QSOP Package, Power Dissipation	566 mW
Vapor Phase (60 s) 215°C	θ <sub>JA</sub> Thermal Impedance	149.97°C/W
	Lead Temperature, Soldering	
Infrared (15 s) 220°C	Vapor Phase (60 s)	215°C
	Infrared (15 s)	220°C

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

Table 4. Truth Table

EN	IN	D1	D2	D3	D4	Function
1	Х	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Disable
0	0	S1A	S2A	S3A	S4A	IN = 0
0	1	S1B	S2B	S3B	S4B	IN = 1

<sup>1</sup> Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

### **ESD CAUTION**

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



# **PIN CONFIGURATION AND FUNCTION DESCRIPTIONS**





### **Table 5. Pin Function Descriptions**

Pin Number	Mnemonic	Description
1	IN	Logic Control Input. The logic level at this input controls the operation of the multiplexers (see Table 4).
2	S1A	A-Side Source Terminal of MUX1. Can be an input or output.
3	S1B	B-Side Source Terminal of MUX1. Can be an input or output.
4	D1	Drain Terminal of MUX1. Can be an input or output.
5	S2A	A-Side Source Terminal of MUX2. Can be an input or output.
6	S2B	B-Side Source Terminal of MUX2. Can be an input or output.
7	D2	Drain Terminal of MUX2. Can be an input or output.
8	GND	Ground Reference.
9	D3	Drain Terminal of MUX3. Can be an input or output.
10	S3B	B-Side Source Terminal of MUX3. Can be an input or output.
11	S3A	A-Side Source Terminal of MUX3. Can be an input or output.
12	D4	Drain Terminal of MUX4. Can be an input or output.
13	S4B	B-Side Source Terminal of MUX4. Can be an input or output.
14	S4A	A-Side Source Terminal of MUX4. Can be an input or output.
15	EN	MUX Enable Logic Input. Enables or disables the multiplexers (see Table 4).
16	V <sub>DD</sub>	Positive Power Supply Voltage.

# TERMINOLOGY

 $\mathbf{V}_{\text{DD}}$ Most positive power supply potential.

IDD Positive supply current.

**GND** Ground (0 V) reference.

**S** Source terminal. Can be either an input or an output.

**D** Drain terminal. Can be either an input or an output.

IN Logic control input.

V<sub>D</sub> (V<sub>s</sub>) Analog voltage on terminals D, S.

 $R_{\rm ON}$  Ohmic resistance between D and S.

 $\mathbf{R}_{\text{FLAT (ON)}}$ Flatness is defined as the difference between the maximum and minimum value of on resistance as measured.

 $\Delta R_{\text{ON}}$  On resistance match between any two channels.

Is (Off) Source leakage current with the switch off.

 $I_{\rm D}$  (Off) Drain leakage current with the switch off.

I<sub>D</sub>, I<sub>S</sub> (On) Channel leakage current with the switch on.

 $\mathbf{V}_{\text{INL}}$ Maximum input voltage for Logic 0.

V<sub>INH</sub> Minimum input voltage for Logic 1.

I<sub>INL</sub> (I<sub>INH</sub>) Input current of the digital input. Cs (Off)

Off switch source capacitance. Measured with reference to ground.

 $C_{\rm D}\left(Off\right)$  Off switch drain capacitance. Measured with reference to ground.

C<sub>D</sub>, C<sub>s</sub> (On) On switch capacitance. Measured with reference to ground.

C<sub>IN</sub> Digital input capacitance.

**t**<sub>ON</sub> Delay time between the 50% and the 90% points of the digital input and switch on condition.

**t**<sub>OFF</sub> Delay time between the 50% and the 90% points of the digital input and switch off condition.

 $t_{\text{BBM}}$  On or off time measured between the 80% points of both switches when switching from one to another.

**Charge Injection** A measure of the glitch impulse transferred from the digital input to the analog output during on/off switching.

**Off Isolation** A measure of unwanted signal coupling through an off switch.

### Crosstalk

A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

**-3 dB Bandwidth** The frequency at which the output is attenuated by 3 dB.

**On Response** The frequency response of the on switch.

**Insertion Loss** The loss due to the on resistance of the switch.

**THD + N** The ratio of the harmonic amplitudes plus noise of a signal to the fundamental.

# **TYPICAL PERFORMANCE CHARACTERISTICS**



Figure 3. Off Isolation vs. Frequency



Figure 4. Crosstalk vs. Frequency

### **TYPICAL APPLICATION**



Figure 5. Audio/Video Switch





Figure 14. Charge Injection

# **OUTLINE DIMENSIONS**



Dimensions shown in inches and (millimeters)

### **ORDERING GUIDE**

Model	Temperature Range	Package Description	Package Option
ADG794BRQZ <sup>1</sup>	−40°C to +85°C	16-Lead Shrink Small Outline Package (QSOP)	RQ-16
ADG794BRQZ-500RL71	-40°C to +85°C	16-Lead Shrink Small Outline Package (QSOP)	RQ-16
ADG794BRQZ-REEL <sup>1</sup>	-40°C to +85°C	16-Lead Shrink Small Outline Package (QSOP)	RQ-16
ADG794BRQZ-REEL7 <sup>1</sup>	−40°C to +85°C	16-Lead Shrink Small Outline Package (QSOP)	RQ-16

 $^{1}$  Z = Pb-free part.

# NOTES



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Rev. 0 | Page 12 of 12